

In re Appln. of MIHASHI et al.
Application No. Unassigned

ABSTRACT AMENDMENTS

Replace the Abstract with:

A ridge waveguide type semiconductor laser ~~of the present invention comprises~~ includes an active layer, semiconductor layers ~~formed~~ on the active layer and having a ridge-shaped waveguide ~~therein~~, an ~~insulation~~ insulating film ~~formed~~ on the semiconductor layer, a first electrode layer in contact with the semiconductor layer through an opening ~~provided~~ in the ~~insulation~~ insulating film, and a second electrode layer ~~formed~~ on the first electrode layer ~~such that it is shaped like stripes~~ having a stripe shape and ~~runs in a direction of extending~~ along the waveguide. A distance from an end face of a resonator of the laser to an edge of the second electrode layer ~~is within~~ does not exceed 20 μm .